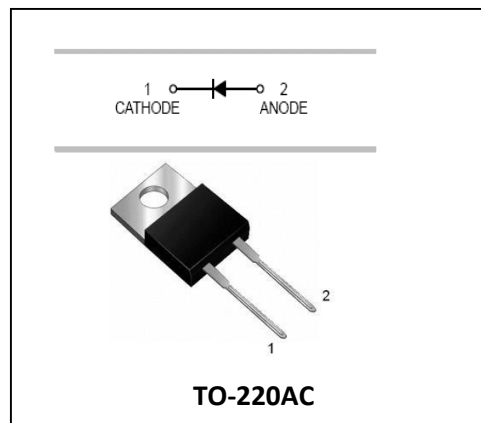


超快恢复二极管 Super Fast Rectifiers

■ 极限值 (Ta=25℃)

- Low cost.
- High current capability.
- Low forward voltage drop.
- Easily cleaned with Alcohol, Isopropanol and Similar solvents.

■ 外形图及引脚排列



参数符号	符号说明	数值	单位
V_{RRM}	Repetitive Peak Reverse Voltage	600	V
V_{RMS}	RMS Voltage	420	V
V_{DC}	DC Blocking Voltage	600	V
$I_{F(AV)}$	Average Forward Rectified Current @TA=100℃	8	A
I_{FSM}	Peak Forward Surge Current 8.3ms Single Half-sine-wave superimposed on Rated Load	100	A
$R_{\theta JC}$	Typical Thermal Resistance Junction to Case	2.0	℃/W
Tj Tstg	Operating Junction and Storage Temperature Range	-65 +175	℃

■ 电参数 (Ta=25℃)

参数符号	符号说明	测试条件	最大值	单位
I_R	Reverse Current	VR=VRRM, TA=25℃ VR=VRRM, TA=150℃	10 500	μA
$V_{(Note1) F}$	Forward Voltage	IF=8A, TA=25℃ IF=8A, TA=150℃	1.50 1.20	V
t_{rr}	Reverse Recovery Time	IF=0.5A, IR=1A, Irr=0.25A	50	ns

Note1: Pulse test pulse width=300μs, duty cycle≤2.0%

■ 特性曲线

FIG.1- MAXIMUM FORWARD CURRENT DERATING CURVE

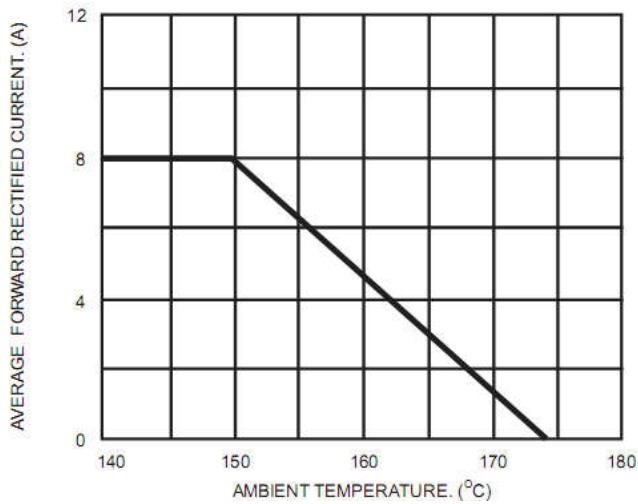


FIG.2- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

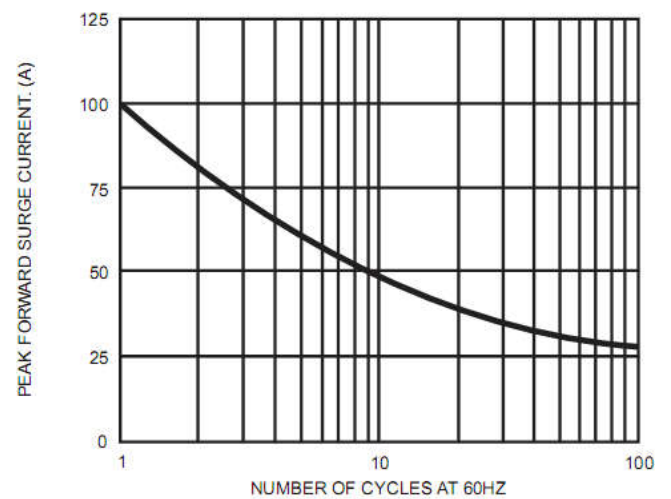


FIG.3- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

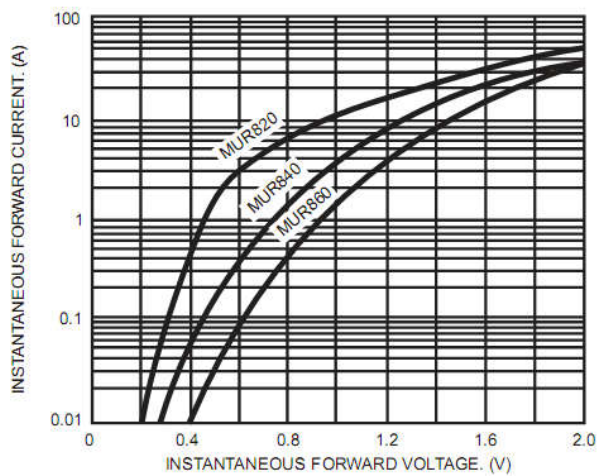
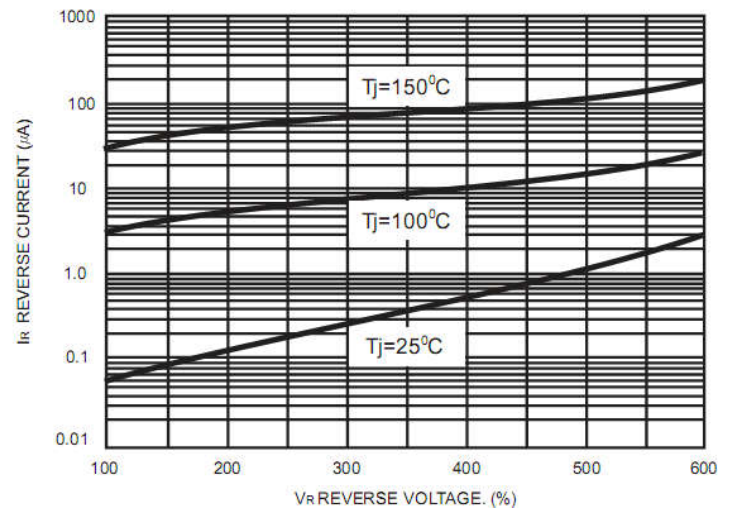


FIG.4- TYPICAL REVERSE CHARACTERISTICS





迈诺斯科技

MUR860G

NOTE:

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shenzhen Minos reserves the right to make changes in this specification sheet and is subject to change without prior notice.

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